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November 2013



FDB14N30 N-Channel UniFETTM MOSFET 300 V, 14 A, 290 mΩ

Features

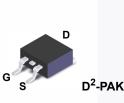
- $R_{DS(on)}$ = 290 m Ω (Max.) @ V_{GS} = 10 V, I_D = 7 A
- Low Gate Charge (Typ. 18 nC)
- Low C_{rss} (Typ.17 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability

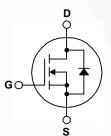
Applications

- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDB14N30TM	Unit	
V _{DSS}	Drain-Source Voltage			300	V
ID	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		14 8.4	A A
I _{DM}	Drain Current	- Pulsed	56	А	
V _{GSS}	Gate-Source voltage			±30	V
E _{AS}	Single Pulsed Avalanche	e Energy	(Note 2)	330	mJ
I _{AR}	Avalanche Current		(Note 1)	14	А
E _{AR}	Repetitive Avalanche Energy		(Note 1)	14	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C			W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
Τ _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FDB14N30TM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max	0.87	
Р	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (1 in ² pad of 2 oz copper), Max.	40	

FDB14N30 — N-C
Channel UniFET TM MOSFE
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•		Device	Pac	Package Reel Size		Тар	Tape Width		Quantity	
		D2-	2-PAK 330mm		24mm		800 units			
Electric	al Char	acteristics T _c =	= 25°C un	less other	vise noted.					
Symbol Parameter				Conditions		Min.	Тур.	Max	Unit	
Off Charac	teristics									
BV _{DSS}	Drain-Sou	rce Breakdown Voltag	le	V _{GS} = 0V,	I _D = 250μA		300			V
ΔBV _{DSS} / ΔT _J	Breakdow Coefficien	n Voltage Temperature t	Э	I _D = 250μ/	A, Referenced to 25°C			0.3		V/∘C
I _{DSS}	Zero Gate	Voltage Drain Current	t		0V, V _{GS} = 0V 0V, T _C = 125°C				1 10	μΑ μΑ
I _{GSSF}	Gate-Body	/ Leakage Current, Fo	orward		/, V _{DS} = 0V				100	nA
I _{GSSR}	Gate-Body	/ Leakage Current, Re	everse	V _{GS} = -30	V, V _{DS} = 0V				-100	nA
On Charac	teristics									
V _{GS(th)}	Gate Thre	shold Voltage		$V_{DS} = V_{GS}$	_S , I _D = 250μA		3.0		5.0	V
R _{DS(on)}	Static Drai On-Resist			V _{GS} = 10\	/, I _D = 7A			0.24	0.29	Ω
9 _{FS}	Forward T	ransconductance		V _{DS} = 40\	/, I _D = 7A			10.5		S
Dynamic C	haracterist	tics								
C _{iss}	Input Capa	acitance		$V_{DS} = 25V, V_{GS} = 0V,$				815	1060	pF
C _{oss}	Output Ca	pacitance		f = 1.0MH	łz			150	195	pF
C _{rss}	Reverse T	ransfer Capacitance						17	25	pF
Switching	Characteris	stics								
t _{d(on)}	Turn-On D	elay Time		V_{DD} = 150V, I_D = 14A R_G = 25 Ω			20	50	ns	
t _r	Turn-On R	lise Time						105	120	ns
t _{d(off)}	Turn-Off D	elay Time						30	70	ns
t _f	Turn-Off F	all Time				(Note 4)		75	160	ns
Qg	Total Gate	Charge		$V_{DS} = 240V, I_D = 14A$ $V_{GS} = 10V$ (Note 4)			18	25	nC	
Q _{gs}	Gate-Sour	ce Charge					4.5		nC	
Q _{gd}	Gate-Drain	n Charge					8		nC	
Drain-Sou	rce Diode C	haracteristics and M	laximum	Ratings						L
I _S	Maximum	Continuous Drain-Sou	urce Diod	e Forward	Current				14	Α
I _{SM}	0		Diode Fo	rward Curr	ent				56	Α
V _{SD}	Drain-Sou	rce Diode Forward Vo	ltage	V _{GS} = 0V,	I _S = 14A				1.4	V
t _{rr}	Reverse R	Recovery Time		V _{GS} = 0V,	I _S = 14A			235		ns
Q _{rr}		Recovery Charge		$dI_F/dt = 10$	$= \frac{d_{\rm g}}{d_{\rm F}/dt} = 100 \text{A}/\mu \text{s}$			1.6		μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

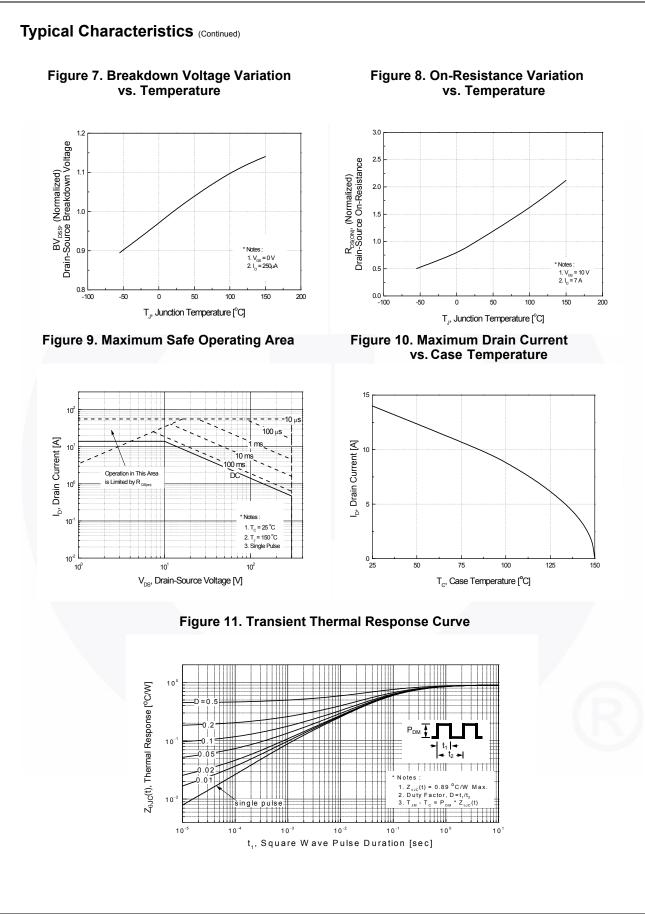
2. L = 2.8mH, I_{AS} = 14A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

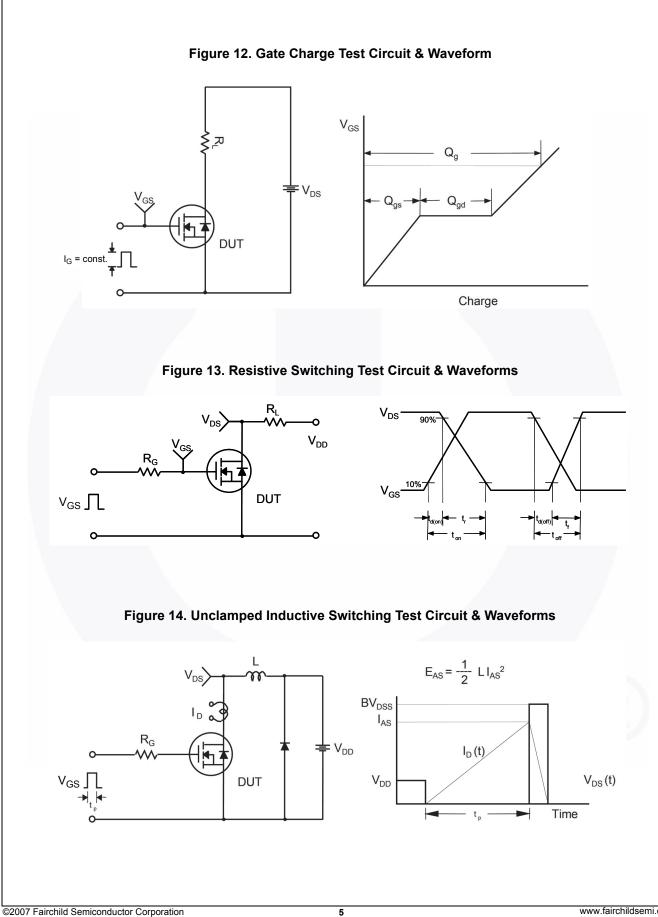
3. $I_{SD} \leq$ 14A, di/dt \leq 200A/µs, $V_{DD} \leq BV_{DSS},$ Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics Figure 1. On-Region Characteristics **Figure 2. Transfer Characteristics** 10 V_{GS} 15.0 V 10.0 V 10 8.0 V 7.0 V 6.5 V 6.0 V I_D, Drain Current [A] I_D, Drain Current [A] 10 5.5 V 10 150°C 10 25°0 * Notes : 1. V_{DS} = 40V 2. 250µs Pulse Test Notes 1. 250µs Pulse Test 10 2. T_c = 25⁰C 10⁰ 10 12 V_{GS}, Gate-Source Voltage [V] 10 10⁰ 10¹ V_{DS}, Drain-Source Voltage [V] Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue 1.3 10 12 Drain-Source On-Resistance 0 0 0 0 1 I_{DR}, Reverse Drain Current [A] 1.0 0.9 V_{GS} = 10\ 10 V_{GS} = 20V 25°C * Notes 1. V_{GS} = 0V 2. 250μs Pulse Test ^{NO}SC 0.2 2 0.1 T, = 25°C * Note 10⁰ ∟ 0.2 1 2.2 2.4 10 20 25 30 35 40 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0 0 5 15 45 $I_{_{D}}$, Drain Current [A] V_{SD}, Source-Drain voltage [V] **Figure 6. Gate Charge Characteristics Figure 5. Capacitance Characteristics** 2000 12 = C_{gs} $_{s} + C_{gd} (C_{ds} = shorted)$ $_{ds} + C_{gd}$ 10 V_{DS} = 60V V_{GS}, Gate-Source Voltage [V] V_{DS} = 150V Capacitances [pF] 8 V_{DS} = 240V 1000 6 * Note 1. V_{gs} = 0 V 2. f = 1 MHz 2 Note : I_D = 14A 0 0 10⁻¹ 10 10 0 2 10 12 14 16 18 20 4 6 8 V_{DS}, Drain-Source Voltage [V] Q_G, Total Gate Charge [nC]

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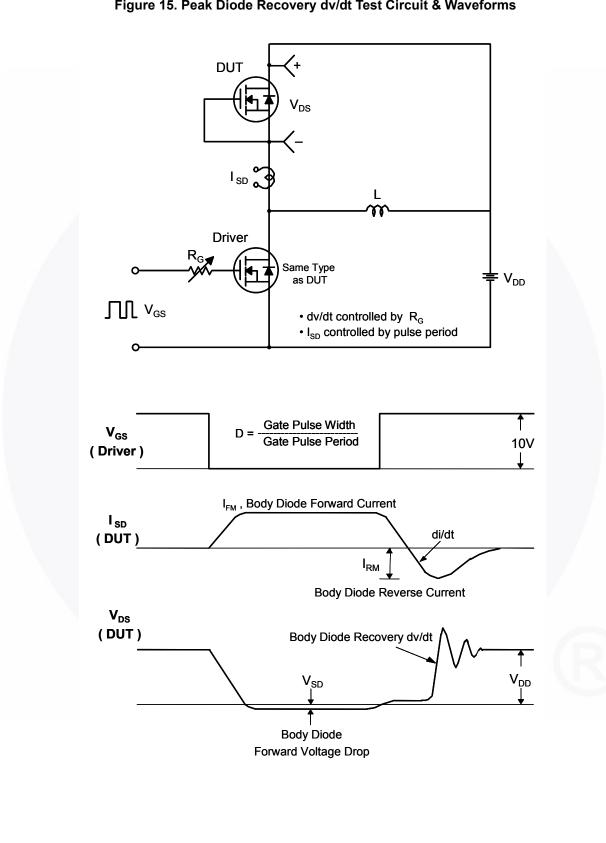
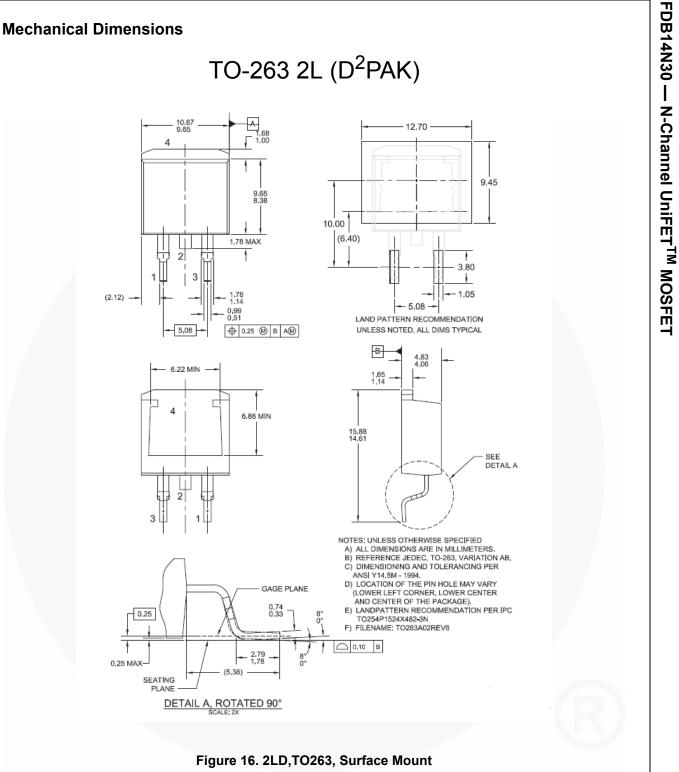


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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Dimension in Millimeters

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